

**DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
50V	1.6Ω @ V <sub>GS</sub> = 10V	360mA
	2.5Ω @ V <sub>GS</sub> = 4.5V	250mA

**Description and Applications**

This new generation MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC converters
- Power-management functions
- Battery operated systems and solid-state relays
- Drivers: relays, solenoids, lamps, hammers, displays, memories, transistors, etc

**Features and Benefits**

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Small Surface-Mount Package
- ESD Protected to 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An automotive-compliant part is available under a separate datasheet ([DMN53D0LDWQ](#))**

**Mechanical Data**

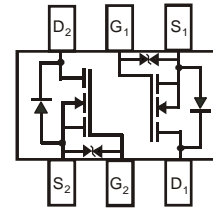
- Package: SOT363
- Package Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208③
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



SOT363 (Standard)



Top View



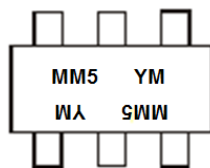
Top View  
Internal Schematic

**Ordering Information** (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMN53D0LDW-7	SOT363 (Standard)	3000	Tape & Reel
DMN53D0LDW-13	SOT363 (Standard)	10000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**



MM5 = Product Type Marking Code  
YM = Date Code Marking  
Y or  $\bar{Y}$  = Year (ex: M = 2025)  
M or  $\bar{M}$  = Month (ex: 9 = September)

**Date Code Key**

Year	2014	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	B	-	M	N	P	R	S	T	U	V	W	X
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V <sub>DSS</sub>	50	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	I <sub>D</sub>	360	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	310	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	411	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	—	—	V	V <sub>GS</sub> = 0, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0
Gate-Body Leakage	I <sub>GSS</sub>	—	—	10	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.8	—	1.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.0	1.6	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 500mA
		—	1.0	2.5		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 200mA
		—	1.4	4.5		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 100mA
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.4	V	V <sub>GS</sub> = 0, I <sub>S</sub> = 500mA
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	46	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	5.3	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	4.0	—	pF	
Total Gate Charge	Q <sub>g</sub>	—	0.6	—	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Source Charge	Q <sub>gs</sub>	—	0.2	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.1	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	2.7	—	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, R <sub>G</sub> = 25Ω, I <sub>D</sub> = 200mA
Turn-On Rise Time	t <sub>R</sub>	—	2.5	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	19	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	11	—	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
6. Short duration pulse test used to minimize self-heating effect.  
7. Guaranteed by design. Not subject to product testing.

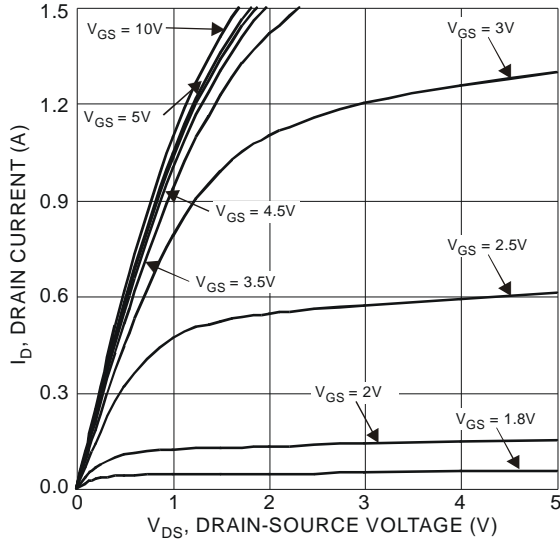


Figure 1 Typical Output Characteristics

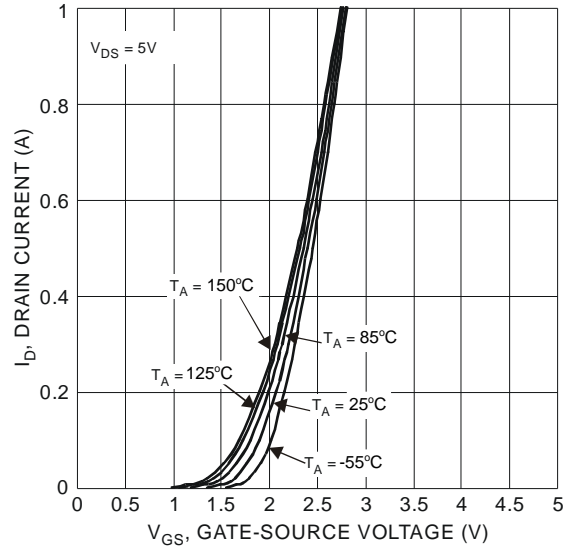


Figure 2 Typical Transfer Characteristics

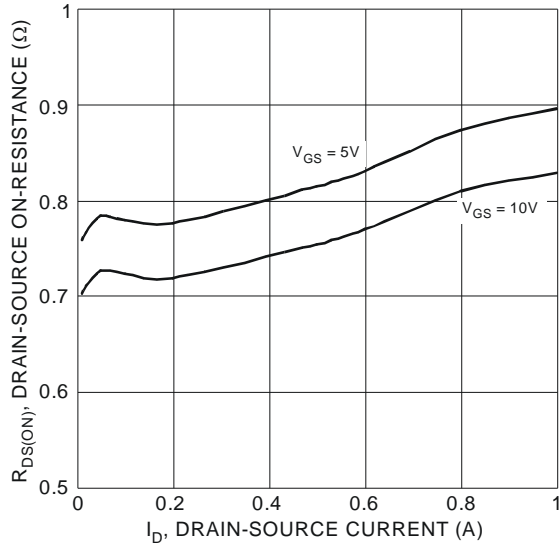


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

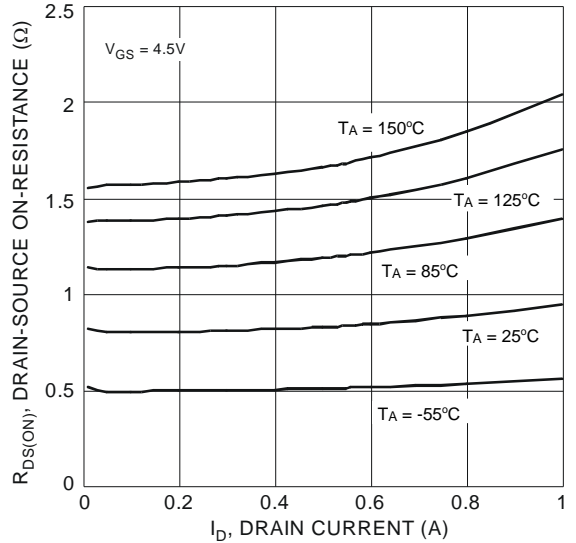


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

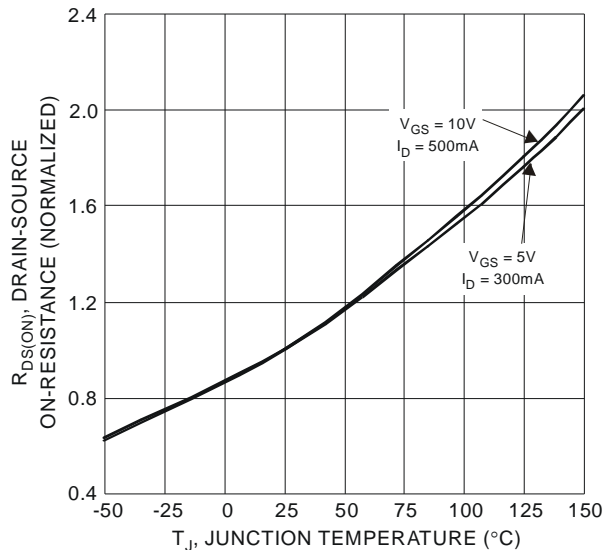


Figure 5 On-Resistance Variation with Temperature

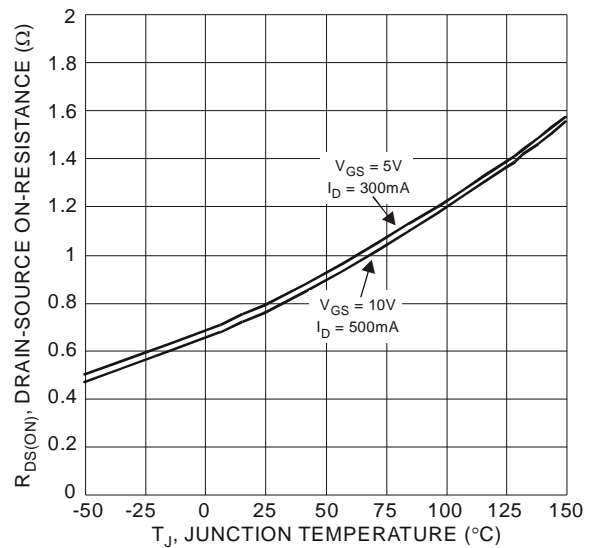


Figure 6 On-Resistance Variation with Temperature

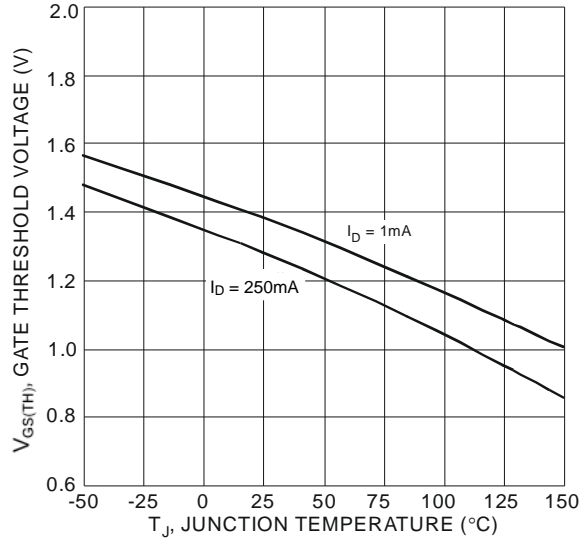


Figure 7 Gate Threshold Variation vs. Junction Temperature

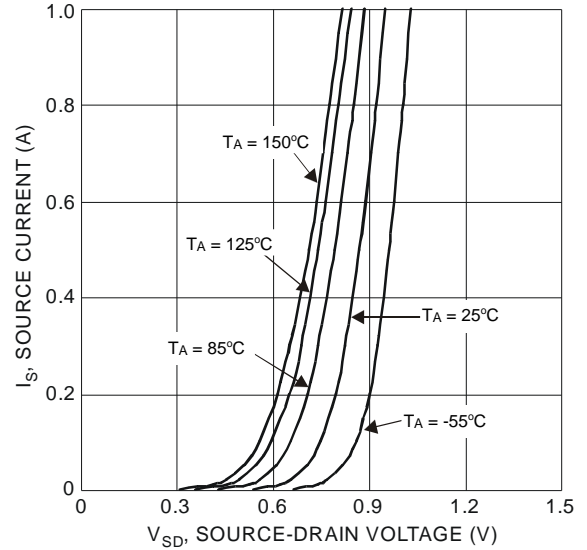


Figure 8 Diode Forward Voltage vs. Current

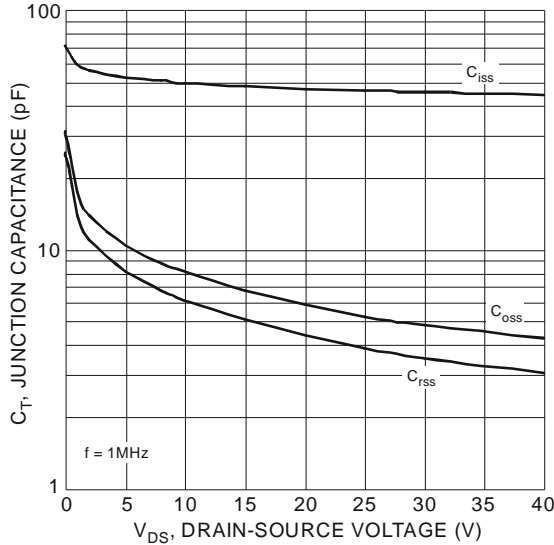


Figure 9 Typical Junction Capacitance

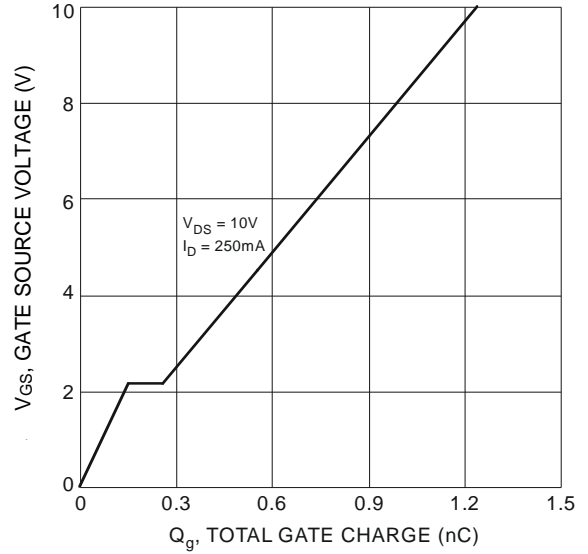
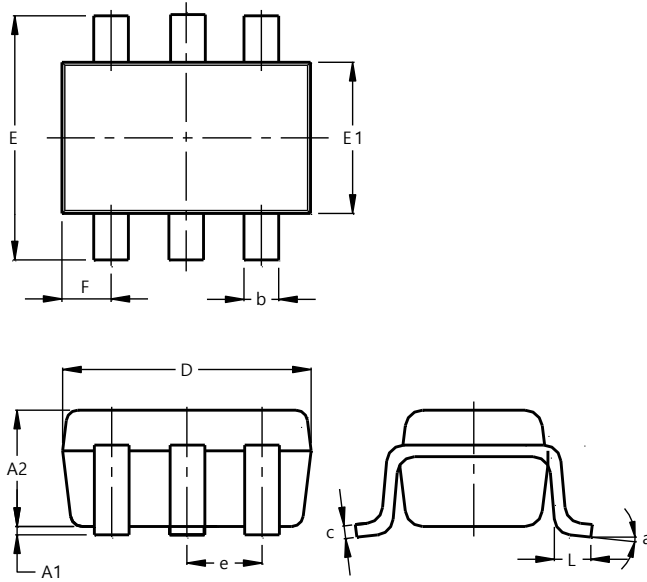


Figure 10 Gate Charge

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)

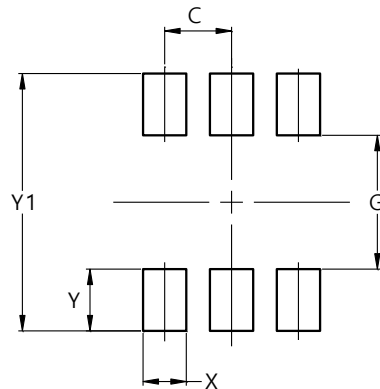


SOT363 (Standard)			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.10	0.35	0.225
c	0.08	0.22	0.15
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
F	0.25	0.45	0.35
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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